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# 2SK3044

## Silicon N-channel power MOSFET

### ■ Features

- Avalanche energy capability guaranteed: EAS > 130 mJ
- Gate-source surrender voltage  $V_{GSS} : \pm 30$  V guaranteed
- High-speed switching
- No secondary breakdown

### ■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

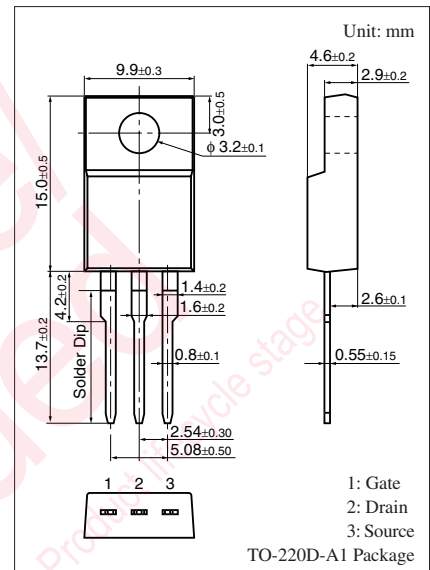
| Parameter                      | Symbol    | Rating                   | Unit             |
|--------------------------------|-----------|--------------------------|------------------|
| Drain-source surrender voltage | $V_{DSS}$ | 450                      | V                |
| Gate-source surrender voltage  | $V_{GSS}$ | $\pm 30$                 | V                |
| Drain current                  | $I_D$     | $\pm 7$                  | A                |
| Peak drain current             | $I_{DP}$  | $\pm 14$                 | A                |
| Avalanche energy capability *  | EAS       | 130                      | mJ               |
| Power dissipation              | $P_D$     | 40                       | W                |
|                                |           | $T_a = 25^\circ\text{C}$ | 2                |
| Channel temperature            | $T_{ch}$  | 150                      | $^\circ\text{C}$ |
| Storage temperature            | $T_{stg}$ | -55 to +150              | $^\circ\text{C}$ |

Note) \*:  $L = 5.4$  mH,  $I_L = 7$  A, 1 pulse

### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

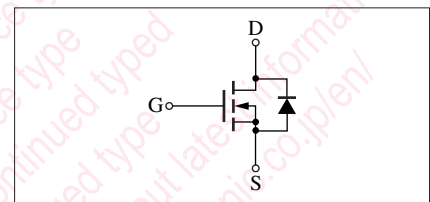
| Parameter  | Symbol         | Conditions  | Min | Typ  | Max     | Unit               |
|--|----------------|---|-----|------|---------|--------------------|
| Drain-source surrender voltage                             | $V_{DSS}$      | $I_D = 1$ mA, $V_{GS} = 0$  | 450 |      |         | V                  |
| Drain-source cutoff current                                | $I_{DSS}$      | $V_{DS} = 360$ V, $V_{GS} = 0$  |     |      | 100     | $\mu\text{A}$      |
| Gate-source cutoff current                                 | $I_{GSS}$      | $V_{GS} = \pm 30$ V, $V_{DS} = 0$                                       |     |      | $\pm 1$ | $\mu\text{A}$      |
| Gate threshold voltage                                     | $V_{th}$       | $V_{DS} = 25$ V, $I_D = 1$ mA   | 2.0 |      | 5.0     | V                  |
| Forward transfer admittance                                | $ Y_{fs} $     | $V_{DS} = 25$ V, $I_D = 4$ A  | 3.0 | 5.0  |         | S                  |
| Drain-source ON resistance                                 | $R_{DS(on)}$   | $V_{GS} = 10$ V, $I_D = 4$ A  |     | 0.56 | 0.75    | $\Omega$           |
| Diode forward voltage                                      | $V_{DF}$       | $I_{DR} = 7$ A, $V_{GS} = 0$  |     |      | -1.7    | V                  |
| Short-circuit forward transfer capacitance (Common source) | $C_{iss}$      | $V_{DS} = 20$ V, $V_{GS} = 0$ , $f = 1$ MHz                             |     | 1300 |         | pF                 |
| Short-circuit output capacitance (Common source)           | $C_{oss}$      |   |     | 160  |         | pF                 |
| Reverse transfer capacitance (Common source)               | $C_{rss}$      |   |     | 70   |         | pF                 |
| Turn-on delay time   | $t_{d(on)}$    | $V_{DD} = 150$ V, $I_D = 4$ A, $R_L = 37.5$ $\Omega$<br>$V_{GS} = 10$ V |     | 25   |         | ns                 |
| Rise time  | $t_r$          |   |     | 45   |         | ns                 |
| Fall time  | $t_f$          |   |     | 50   |         | ns                 |
| Turn-off delay time  | $t_{d(off)}$   |   |     | 150  |         | ns                 |
| Thermal resistance (ch-c)                                  | $R_{th(ch-c)}$ |   |     |      | 3.1     | $^\circ\text{C/W}$ |
| Thermal resistance (ch-a)                                  | $R_{th(ch-a)}$ |   |     |      | 62.5    | $^\circ\text{C/W}$ |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

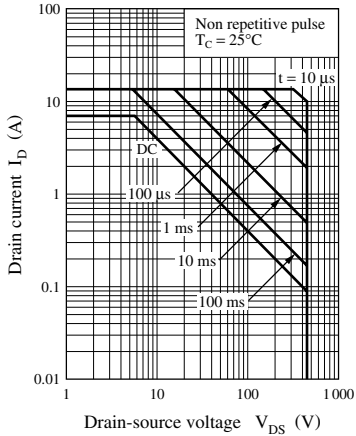


Marking Symbol: K3044

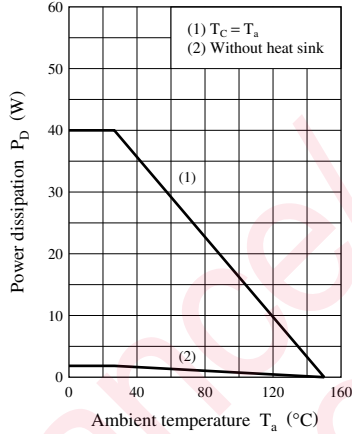
Internal Connection



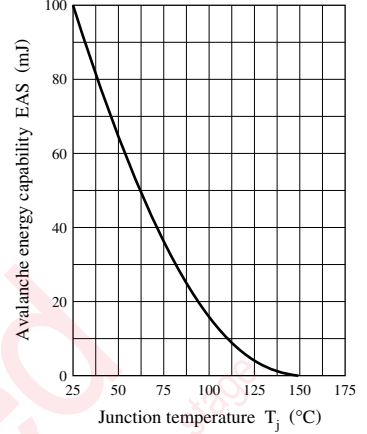
Safe operation area



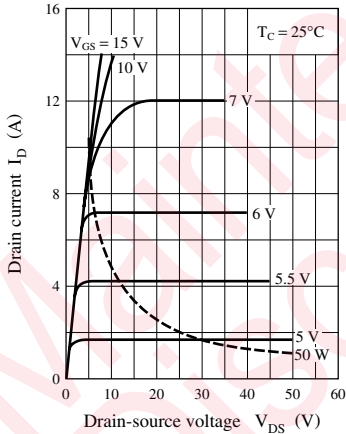
$P_D - T_a$



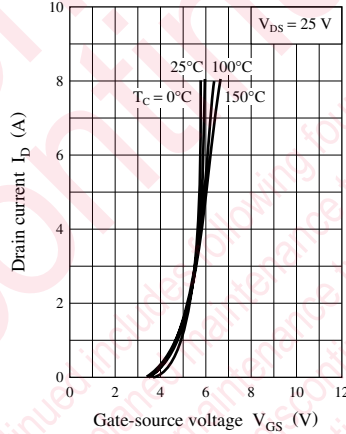
EAS —  $T_j$



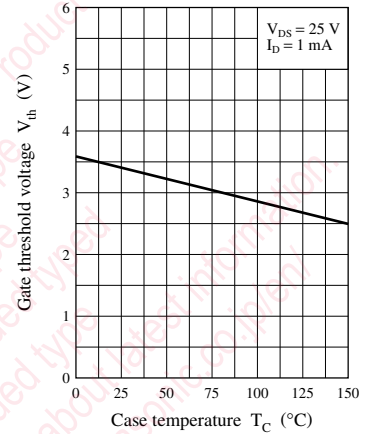
$I_D - V_{DS}$



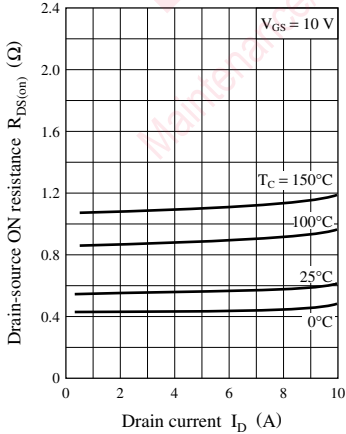
$I_D - V_{GS}$



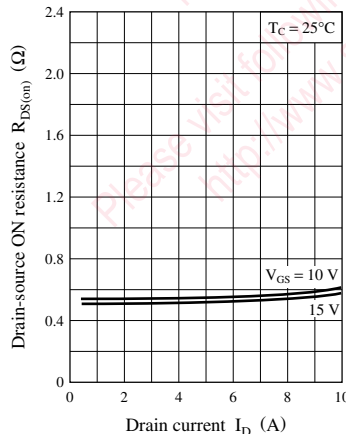
$V_{th} - T_C$



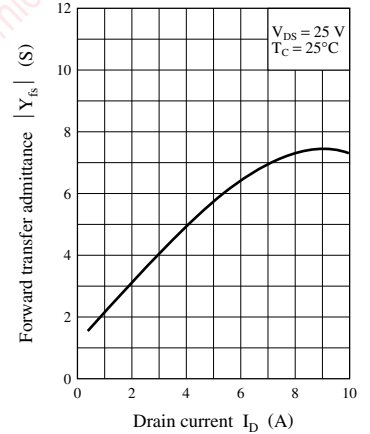
$R_{DS(on)} - I_D$



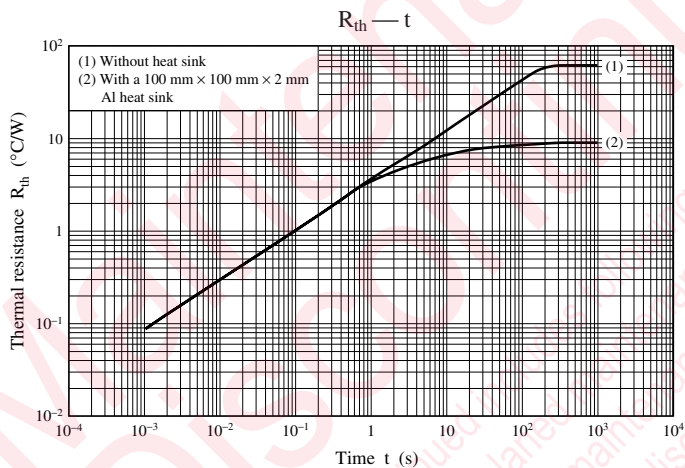
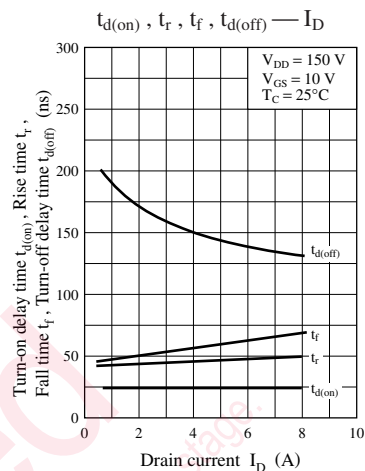
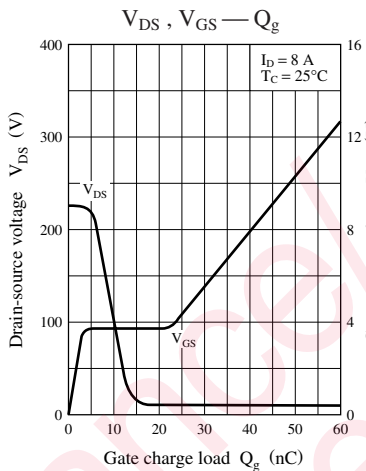
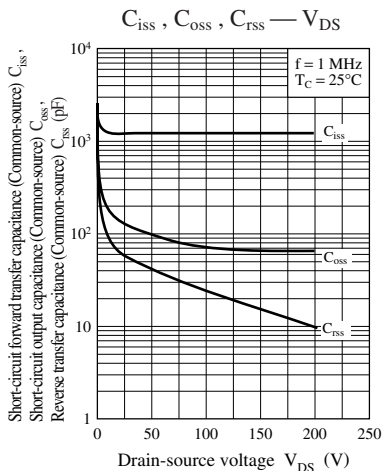
$R_{DS(on)} - I_D$



$|Y_{fs}| - I_D$







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